Ordering number : ENN7010

N-Channel Silicon MOSFET

MCH3406

Ultrahigh-Speed Switching Applications

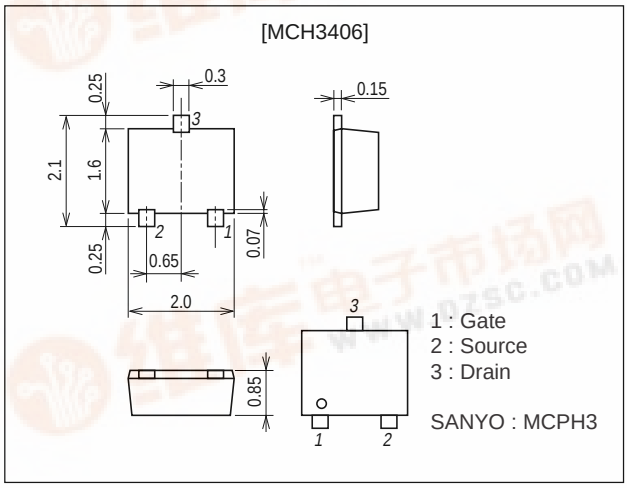
Features

- Low ON-state resistance.
- Ultrahigh-speed switching.
- 1.8V drive.

Package Dimensions

unit : mm

2167A



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		20	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		3	A
Drain Current (Pulse)	I_{DP}	PW≤10µs, duty cycle≤1%	12	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (900mm²×0.8mm)	1	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0	20			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V, V_{GS}=0			1	µA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0			±10	µA
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=1mA	0.4		1.3	V
Forward Transfer Admittance	|yfs|	V_{DS}=10V, I_D=1.5A	3.9	5.6		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=1.5A, V_{GS}=4V		48	63	mΩ
	R_{DS}(on)2	I_D=1A, V_{GS}=2.5V		58	82	mΩ
	R_{DS}(on)3	I_D=0.5A, V_{GS}=1.8V		72	110	mΩ

Marking : KF

Continued on next page.

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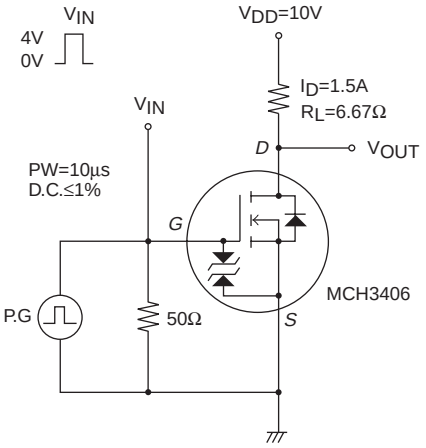
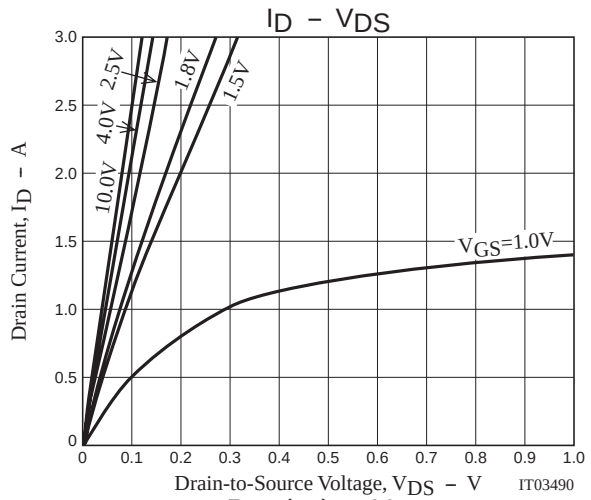
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

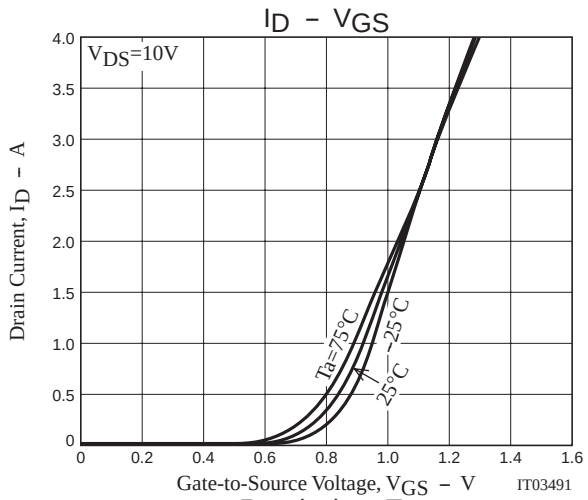
Continued from preceding page.

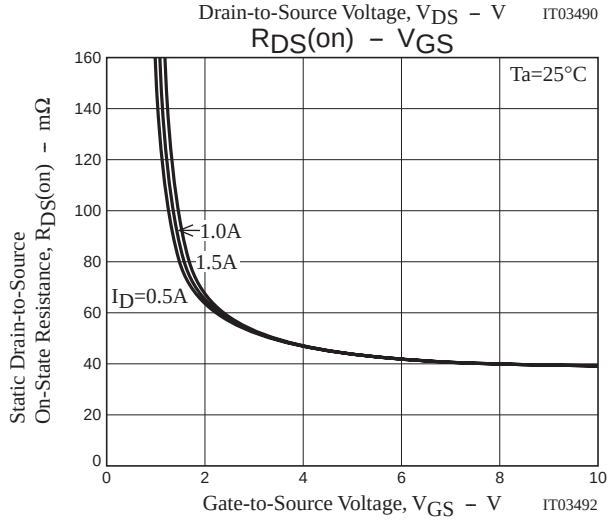
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V_{DS}=10V, f=1MHz		280		pF
Output Capacitance	Coss	V_{DS}=10V, f=1MHz		60		pF
Reverse Transfer Capacitance	Crss	V_{DS}=10V, f=1MHz		38		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit		13		ns
Rise Time	t_r	See specified Test Circuit		35		ns
Turn-OFF Delay Time	t_d(off)	See specified Test Circuit		35		ns
Fall Time	t_f	See specified Test Circuit		25		ns
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=4V, I_D=3A		8.8		nC
Gate-to-Source Charge	Qgs	V_{DS}=10V, V_{GS}=4V, I_D=3A		0.85		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=10V, V_{GS}=4V, I_D=3A		0.85		nC
Diode Forward Voltage	V_{SD}	I_S=3A, V_{GS}=0		0.82	1.2	V

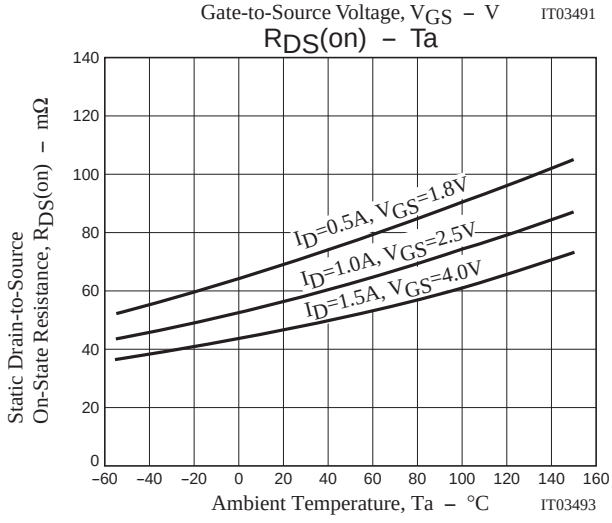
Switching Time Test Circuit

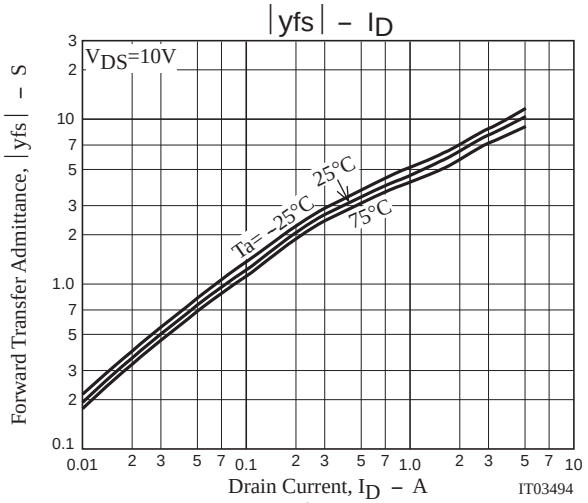


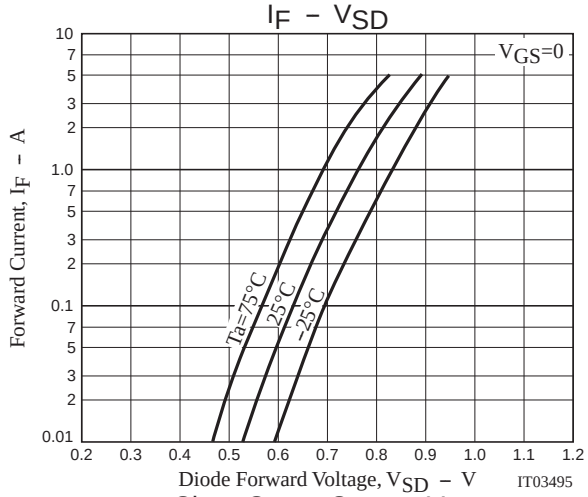


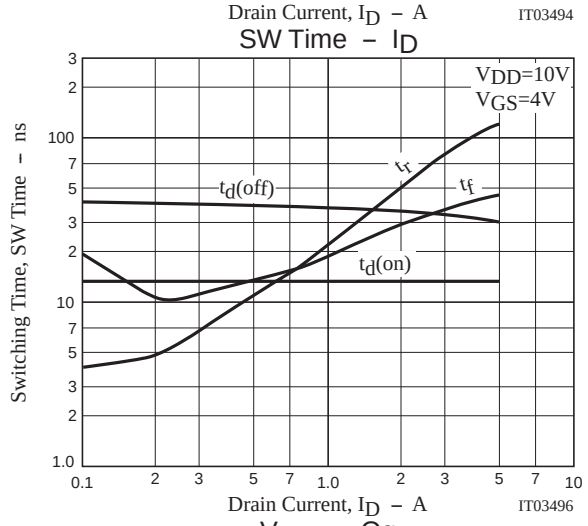


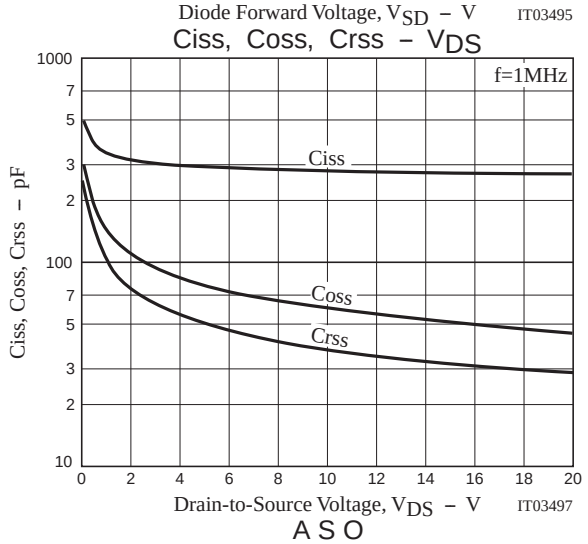


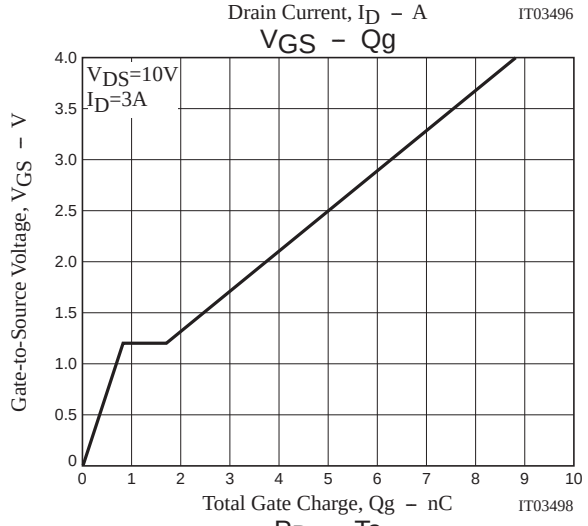


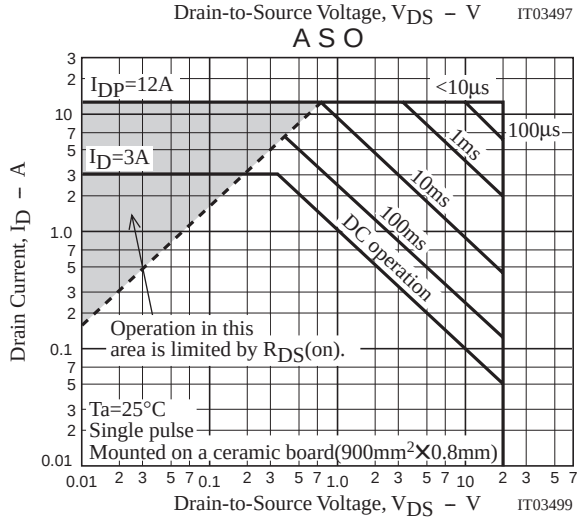

|yfs| – ID
VDS=10V
Ta=–25°C
25°C
75°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT03494

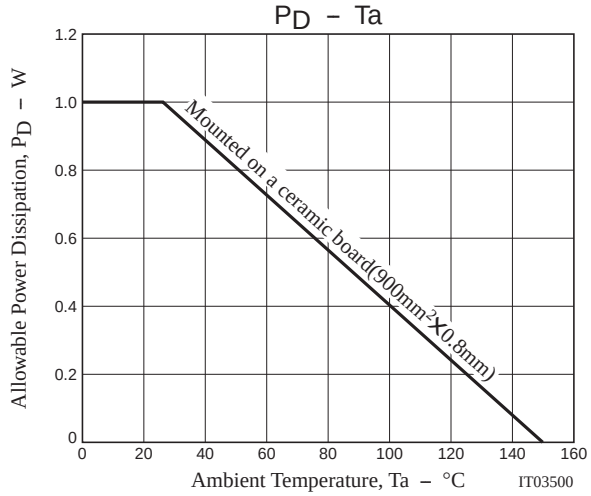

IF – VSD
VGS=0
Ta=75°C
25°C
–25°C
Forward Current, IF – A
Diode Forward Voltage, VSD – V
IT03495


SW Time – ID
VDD=10V
VGS=4V
tr
tf
td(off)
td(on)
Switching Time, SW Time – ns
Drain Current, ID – A
IT03496


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT03497


VGS – Qg
VDS=10V
ID=3A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT03498


A S O
IDP=12A
ID=3A
<10μs
100μs
1ms
10ms
100ms
DC operation
Operation in this
area is limited by RDS(on).
Ta=25°C
Single pulse
Mounted on a ceramic board(900mm2×0.8mm)
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT03499


PD – Ta
Mounted on a ceramic board(900mm2×0.8mm)
Allowable Power Dissipation, PD – W
Ambient Temperature, Ta – °C
IT03500